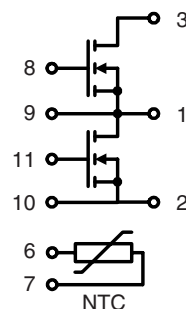


Dual Power HiPerFET™ Module

Phaseleg Configuration

$$\begin{aligned} V_{DSS} &= 100 \text{ V} \\ I_{D25} &= 680 \text{ A} \\ R_{DS(on)} &= 1.8 \text{ m}\Omega \end{aligned}$$

Preliminary Data

MOSFET $T_1 + T_2$

Symbol	Conditions	Maximum Ratings
V_{DSS}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	100 V
V_{GS}		± 20 V
I_{D25}	$T_C = 25^{\circ}\text{C}$ ①	680 A
I_{D80}	$T_C = 80^{\circ}\text{C}$ ①	500 A
I_{F25}	(diode) $T_C = 25^{\circ}\text{C}$ ①	680 A
I_{F80}	(diode) $T_C = 80^{\circ}\text{C}$ ①	500 A

Features

- HiPerFET™ technology
 - low R_{DSon}
 - unclamped inductive switching (UIS) capability
 - dv/dt ruggedness
 - fast intrinsic reverse diode
 - low gate charge
- thermistor for internal temperature measurement
- package
 - low inductive current path
 - screw connection to high current main terminals
 - use of non interchangeable connectors for auxiliary terminals possible
 - Kelvin source terminals for easy drive
 - isolated DCB ceramic base plate

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
R_{DSon}	$V_{GS} = 10\text{ V}; I_D = I_{D80}$	1.8	2.2	m Ω
V_{GSth}	$V_{DS} = 20\text{ V}; I_D = 30\text{ mA}$	2	4	V
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}; V_{GS} = 0\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.5	1	mA mA
I_{GSS}	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\text{ V}$		1	μA
Q_g Q_{gs} Q_{gd}	$\left. \begin{array}{l} \\ \\ \end{array} \right\} V_{GS} = 10\text{ V}; V_{DS} = 75\text{ V}; I_D = I_{D80}$	1440 200 680		nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$\left. \begin{array}{l} \\ \\ \\ \end{array} \right\} V_{GS} = 10\text{ V}; V_{DS} = 0.5 \cdot V_{DSS};$ $I_D = I_{D80}; R_G = 0.47\text{ }\Omega$	150 250 400 200		ns ns ns ns
V_F	(diode) $I_F = 650\text{ A}; V_{GS} = 0\text{ V}$	1.2	1.5	V
t_{rr}	(diode) $I_F = 650\text{ A}; -di/dt = 500\text{ A}/\mu\text{s}; V_{DS} = \frac{1}{2} V_{DSS}$	300		ns
R_{thJC} R_{thJS}	with heat transfer paste	0.12	0.08	K/W K/W

① additional current limitation by external leads

IXYS reserves the right to change limits, test conditions and dimensions.

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Applications

- converters with high power density for
 - main and auxiliary AC drives of electric vehicles
 - 4 quadrant DC drives
 - power supplies

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^{\circ}\text{C}$		2200	Ω
$B_{25/100}$			3560	K

Module

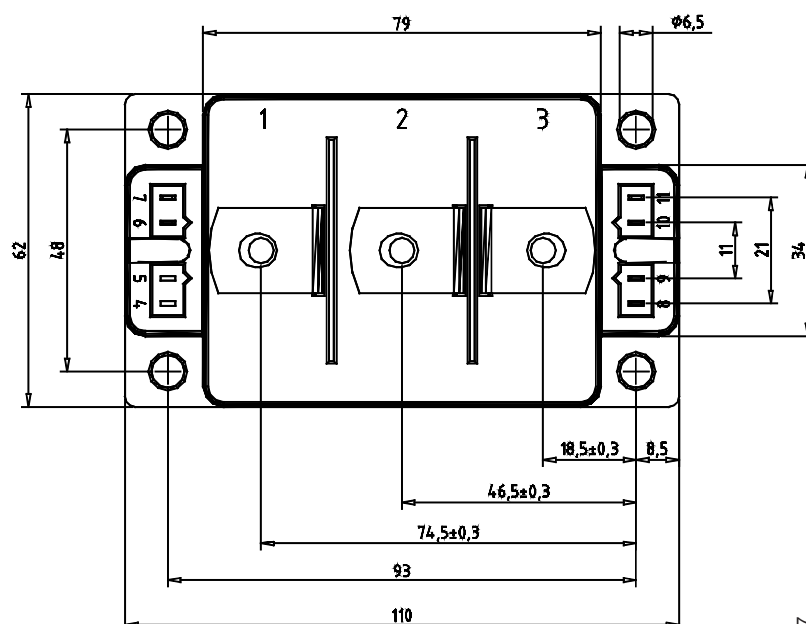
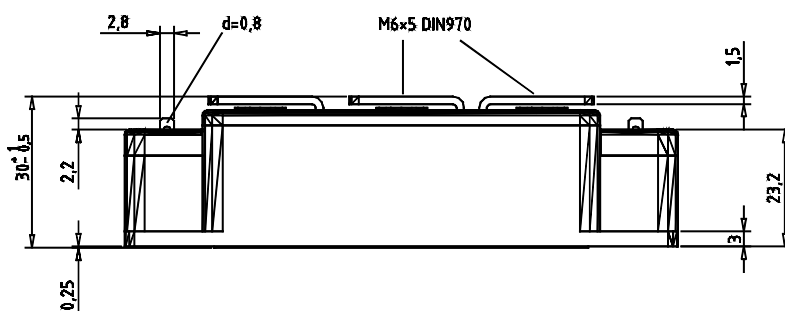
Symbol	Conditions	Maximum Ratings		
T_{VJ}		-40...+150	$^{\circ}\text{C}$	
T_{stg}		-40...+125	$^{\circ}\text{C}$	
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	3600	V~	
M_d	Mounting torque (M6)	2.25 - 2.75	Nm	
	Terminal connection torque (M6)	4.5 - 5.5	Nm	

Symbol	Conditions	Characteristic Values			Dimensions in mm (1 mm = 0.0394")
		min.	typ.	max.	
Weight			250		g

Optional accessories for modules

keyed twin plugs
(UL758, style 1385, CSA class 5851,
guide 460-1-1)

- Type ZY180L with wire length 350mm
– for pins 4 (yellow wire) and 5 (red wire)
– for pins 11 (yellow wire) and 10 (red wire)
- Type ZY180R with wire length 350mm
– for pins 7 (yellow wire) and 6 (red wire)
– for pins 8 (yellow wire) and 9 (red wire)



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